TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HC573AP,TC74HC573AF,TC74HC573AFW

#### Octal D-Type Latch with 3-State Output

The TC74HC573A is a high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its 8-bit D-type latche is controlled by a latch enable input (LE) and a output enable input (  $\overline{OE}$  ).

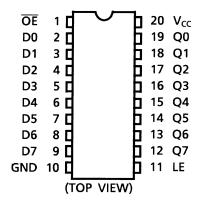
When the  $\overline{\,{
m OE}\,}$  input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

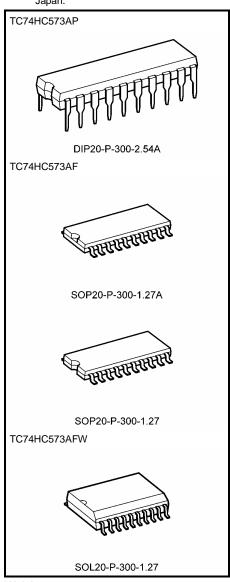
#### **Features**

- High speed:  $t_{pd} = 13 \text{ ns (typ.)}$  at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $ICC = 4 \mu A \text{ (max)}$  at  $Ta = 25^{\circ}C$
- High noise immunity: VNIH = VNIL = 28% VCC (min)
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 6 mA (min)
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 6 V
- Pin and function compatible with 74LS573

#### **Pin Assignment**



Note: xxxFW (JEDEC SOP) is not available in Japan.



Weight

 DIP20-P-300-2.54A
 : 1.30 g (typ.)

 SOP20-P-300-1.27A
 : 0.22 g (typ.)

 SOP20-P-300-1.27
 : 0.22 g (typ.)

 SOL20-P-300-1.27
 : 0.46 g (typ.)

# **IEC Logic Symbol**

OE (1) LE (11)	EN C 1	
$\begin{array}{c} DO \\ \hline (2) \\ \hline (3) \\ \hline (4) \\ \hline (2) \\ \hline (4) \\ \hline (5) \\ \hline (5) \\ \hline (6) \\ \hline (7) \\ \hline (8) \\ \hline (9) \\ \hline (7) \\ \hline (9) \\ \hline \end{array}$	1D ▷ ▽	(19) Q0 (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

#### **Truth Table**

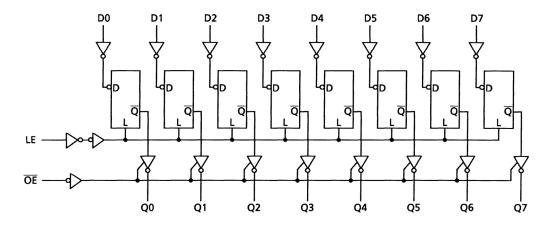
	Output		
ŌE	LE	D	Q
Н	Χ	Х	HZ
L	L	Х	Q <sub>n</sub>
L	Н	L	L
L	Н	Н	Н

X: Don't care

HZ: High impedance

Q<sub>n</sub>: Q outputs are latched at the time when the LE input is taken to a low logic level.

### **System Diagram**



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#### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7	V
DC input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	−0.5 to V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	±20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	l <sub>OUT</sub>	±35	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	P <sub>D</sub>	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C shall be applied until 300 mW.

#### **Recommended Operating Conditions (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	Vcc	2 to 6	V
Input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
		0 to 1000 (V <sub>CC</sub> = 2.0 V)	
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 500 (V <sub>CC</sub> = 4.5 V)	ns
		0 to 400 (V <sub>CC</sub> = 6.0 V)	

Note: The recommended operating conditions are required to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.



### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol		Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
	2, 11			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
				2.0	1.50	_	_	1.50	_	
High-level input voltage	V <sub>IH</sub>		_	4.5	3.15	_	_	3.15	_	V
				6.0	4.20	_	_	4.20	_	
				2.0	_	_	0.50	_	0.50	
Low-level input voltage	V <sub>IL</sub>		_	4.5	_	_	1.35	_	1.35	V
				6.0	_	_	1.80	_	1.80	
				2.0	1.9	2.0	_	1.9	_	
	voн		$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	
High-level output voltage		VIN = VIH or VIL		6.0	5.9	6.0	_	5.9	_	V
			$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -7.8 \text{ mA}$	6.0	5.68	5.80	_	5.63	_	
	VoL			2.0	_	0.0	0.1	_	0.1	
		V <sub>OL</sub> V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
Low-level output voltage				6.0	_	0.0	0.1	_	0.1	V
			I <sub>OL</sub> = 6 mA	4.5	_	0.17	0.26	_	0.33	
			$I_{OL} = 7.8 \text{ mA}$	6.0	_	0.18	0.26	_	0.33	
3-state output off-state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		6.0	_	_	±0.5	_	±5.0	μА
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		6.0			±0.1	_	±1.0	μА
Quiescent supply current	Icc	V <sub>IN</sub> = V <sub>CC</sub> o	r GND	6.0	_	_	4.0	_	40.0	μА

### Timing Requirements (input: $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Test Condition	Ta = 25°C		Ta = -40 to 85°C	Unit	
			V <sub>CC</sub> (V)	Тур.	Limit	Limit	
Minimum pulse width			2.0	_	75	95	
	tw (H)	_	4.5	_	15	19	ns
(LE)			6.0		13	16	
Minimum set-up time			2.0	_	50	65	
(data)	t <sub>s</sub>	_	4.5	_	10	13	ns
(data)			6.0		9	11	
Minimum hold time			2.0		5	5	
(data)	t <sub>h</sub>	_	4.5	_	5	5	ns
(uata)			6.0	_	5	5	



#### AC Characteristics (input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit				
,			CL (pF)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max				
Output transition time	t <sub>TLH</sub>	_	50	2.0 4.5 6.0		20 6 5	60 12 10	_	75 15 13	ns			
			50	2.0 4.5	_	50 15	115 23		145 29				
Propagation delay time (LE-Q)	<sup>t</sup> pLH <sup>t</sup> pHL	_	150	6.0 2.0 4.5	<u> </u>	13 60 20	20 155 31		25 195 39	ns			
				6.0	_	17 42	26 110	_	33				
Propagation delay	<sup>t</sup> pLH		50	2.0 4.5 6.0		14 12	22 19	_ _ _	140 28 24				
(D-Q)	t <sub>pHL</sub>	_	150	2.0 4.5 6.0		57 19 16	150 30 26	_	190 38 32	ns			
	t <sub>n</sub> zı	t <sub>o</sub> zl.	t <sub>D</sub> ZL	<sup>t</sup> pZL		50	2.0 4.5 6.0		55 17 14	140 28 24		175 35 30	
Output enable time tpZH		$R_L = 1 \text{ k}\Omega$	150	2.0 4.5 6.0	_ _ _	66 22 19	180 36 31	_ _ _	225 45 38	ns			
Output disable time	<sup>t</sup> pLZ <sup>t</sup> pHZ	$R_L = 1 \text{ k}\Omega$	50	2.0 4.5 6.0	_ _ _	40 17 15	125 25 21	_ _ _	155 31 26	ns			
Input capacitance	C <sub>IN</sub>	_	_	•	_	5	10	_	10	pF			
Output capacitance	C <sub>OUT</sub>	_	_		_	10	_	_	_	pF			
Power dissipation capacitance	C <sub>PD</sub> (Note)	-	_		_	51	_	_	_	pF			

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

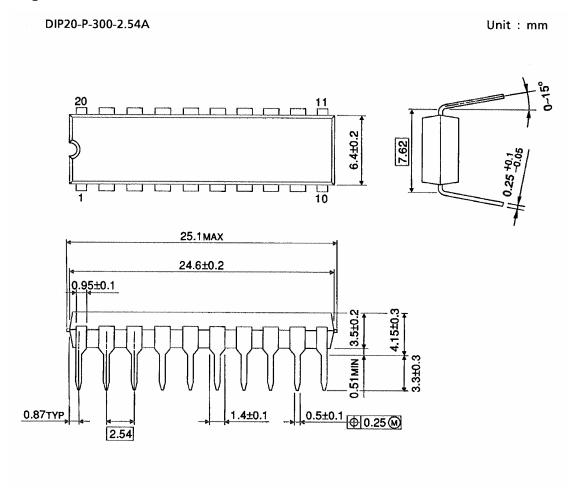
$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per latch)

And the total  $C_{\mbox{\scriptsize PD}}$  when n pcs. of latch operate can be gained by the following equation:

$$C_{PD}$$
 (total) = 33 + 18 · n



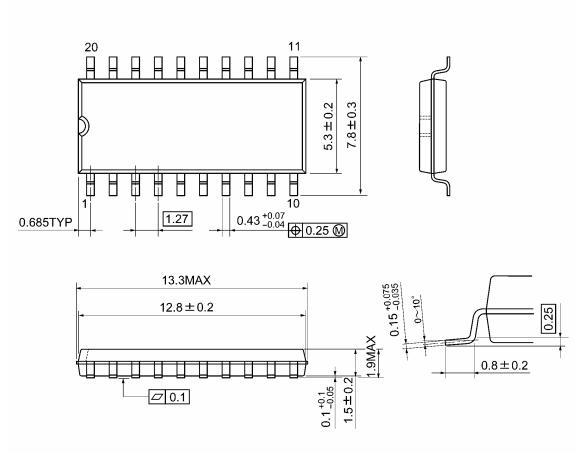
# **Package Dimensions**



Weight: 1.30 g (typ.)

# **Package Dimensions**

SOP20-P-300-1.27A Unit: mm

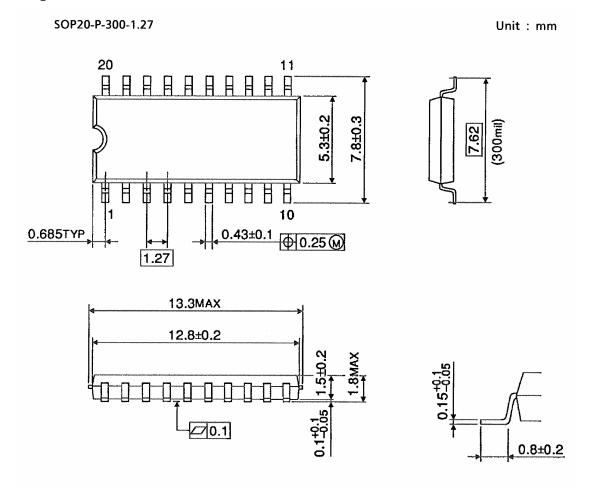


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Weight: 0.22 g (typ.)



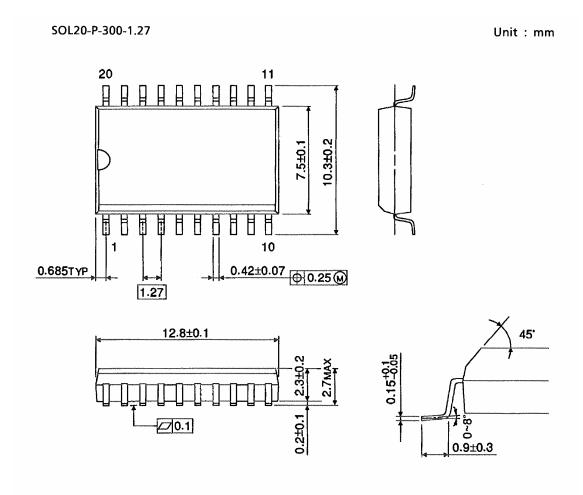
### **Package Dimensions**



Weight: 0.22 g (typ.)



# **Package Dimensions (Note)**



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Note: This package is not available in Japan.

Weight: 0.46 g (typ.)

Note: Lead (Pb)-Free Packages

DIP20-P-300-2.54A SOP20-P-300-1.27A

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